



### 100V N-Channel Enhancement Mode MOSFET - ESD Protected

Voltage

100 V

Current

300mA

#### **Features**

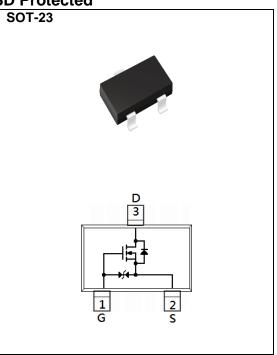
- $R_{DS(ON)}$ ,  $V_{GS}@10V$ ,  $I_D@300mA<6\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}@4.5V$ ,  $I_D@200mA<9\Omega$
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

• Case: SOT-23 Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0003 ounces, 0.0084 grams



### **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage	V <sub>DS</sub>	100	V		
Gate-Source Voltage	V <sub>GS</sub>	<u>+</u> 20			
Continuous Drain Current(Note 4)		I <sub>D</sub>	300	mA	
Pulsed Drain Current <sup>(Note 1)</sup>		I <sub>DM</sub>	800		
Power Dissipation	T <sub>a</sub> =25°C	P <sub>D</sub>	500	mW	
	Derate above 25°C		4	mW/°C	
Operating Junction and Storage Temperature Range		TJ,TsTG	-55~150	°C	
Typical Thermal Resistance					
- Junction to Ambient <sup>(Note 3,4)</sup>	R <sub>θJA</sub>	250	°C/W		





# Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	100	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1.5	1.77	2.5	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =300mA	-	4	6	Ω
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =200mA	-	4.2	9	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =80V, V <sub>GS</sub> =0V	-	-	1	uA
Gate-Source Leakage Current	Igss	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 10	uA
Dynamic <sup>(Note 5)</sup>						
Total Gate Charge	$\mathbf{Q}_{g}$	V <sub>DS</sub> =30V, I <sub>D</sub> =200mA, V <sub>GS</sub> =10V <sup>(Note 1,2)</sup>	-	1.8	-	nC
Gate-Source Charge	Qgs		-	0.4	-	
Gate-Drain Charge	$Q_{gd}$		-	0.3	-	
Input Capacitance	Ciss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHZ	-	45	-	pF
Output Capacitance	Coss		-	14	-	
Reverse Transfer Capacitance	Crss		-	7.8	-	
Turn-On Delay Time	td <sub>(on)</sub>	$\begin{array}{c} V_{DD}{=}30V,\ I_{D}{=}200mA,\\ V_{GS}{=}10V,\\ R_{G}{=}6\Omega^{(Note\ 1,2)} \end{array}$	-	3.4	-	ns
Turn-On Rise Time	tr		-	19	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	8.2	-	
Turn-Off Fall Time	tf		-	20	-	
Drain-Source Diode						
Maximum Continuous Drain-Source			-	-	400	mA
Diode Forward Current	Is					
Diode Forward Voltage	$V_{\text{SD}}$	I <sub>S</sub> =400mA, V <sub>GS</sub> =0V	-	0.9	1.3	V

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing.





#### TYPICAL CHARACTERISTIC CURVES

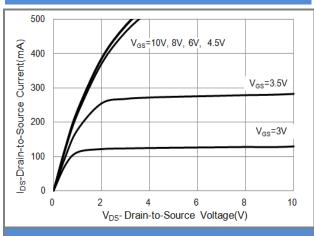


Fig.1 On-Region Characteristics

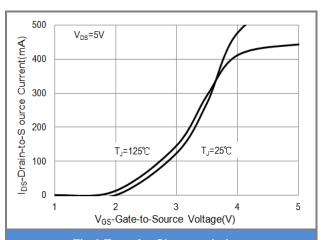


Fig.2 Transfer Characteristics

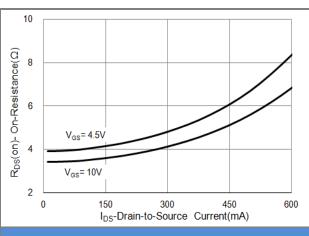


Fig.3 On-Resistance vs. Drain Current

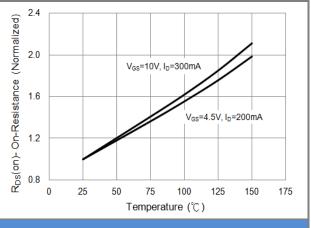
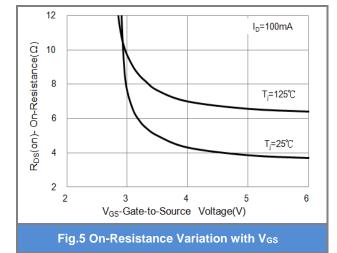
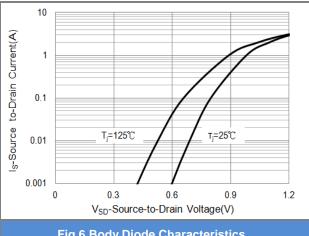


Fig.4 On-Resistance vs. Junction temperature



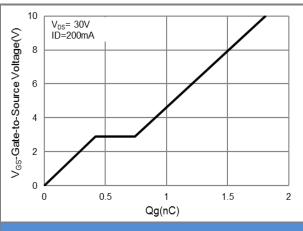


**Fig.6 Body Diode Characteristics** 





#### **TYPICAL CHARACTERISTIC CURVES**



**Fig.7 Gate-Charge Characteristics** 

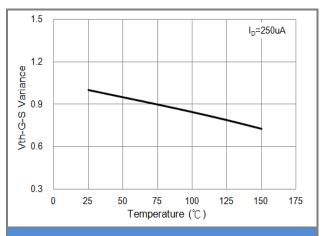


Fig.8 Threshold Voltage Variation with Temperature

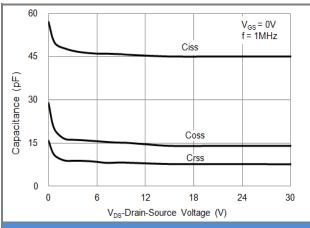


Fig.9 Capacitance vs. Drain-Source Voltage

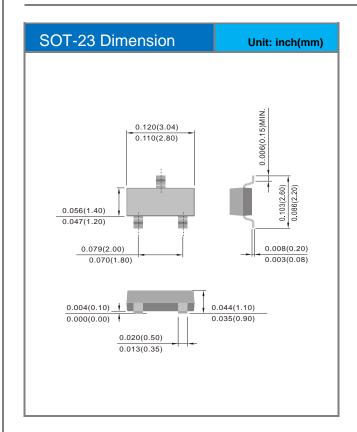


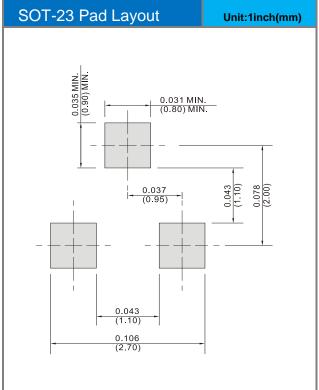


### Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJA3476-AU_R1_000A1	SOT-23	3K pcs / 7" reel	A76	Halogen free RoHS compliant

# **Packaging Information & Mounting Pad Layout**









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